Silicon PNP Power Transistors 2SB747

DESCRIPTION

·With TO-220C package
·Complement to type 2SD812
·Wide area of safe operation

APPLICATIONS

·High power amplifier applications
·Suitable for 15~20W home stereo output amplifier and voltage regulator

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

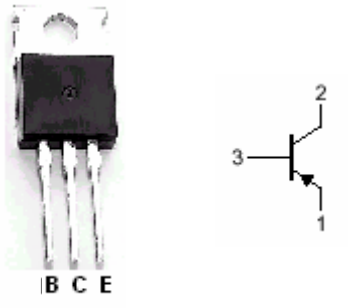

Fig.1 simplified outline (TO-220) and symbol

Absolute maximum ratings(Ta=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-80	V
V_{CEO}	Collector-emitter voltage	Open base	-80	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-5	A
I_{CM}	Collector current-peak		-8	A
P_C	Collector dissipation	T_C=25□	40	W
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-50~150	□

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V_{CEsat}	Collector-emitter saturation voltage	I_C=-3A; I_B=-0.3A			-2.0	V
V_{BE}	Base-emitter on voltage	I_C=-3A ; V_{CE}=-5V			-1.8	V
I_{CBO}	Collector cut-off current	V_{CB}=-80V; I_E=0			-50	μA
I_{EBO}	Emitter cut-off current	V_{EB}=-3V; I_C=0			-50	μA
h_{FE-1}	DC current gain	I_C=-20mA ; V_{CE}=-5V	20			
h_{FE-2}	DC current gain	I_C=-1A ; V_{CE}=-5V	40		200	
h_{FE-3}	DC current gain	I_C=-3A ; V_{CE}=-5V	20			
C_{OB}	Output capacitance	I_E=0 ; V_{CB}=-10V; f=1MHz		190		pF
f_T	Transition frequency	I_C=-0.5A ; V_{CE}=-5V		7		MHz

◆ **h_{FE-2}Classifications**

R	Q	P
40-80	60-120	100-200

PACKAGE OUTLINE

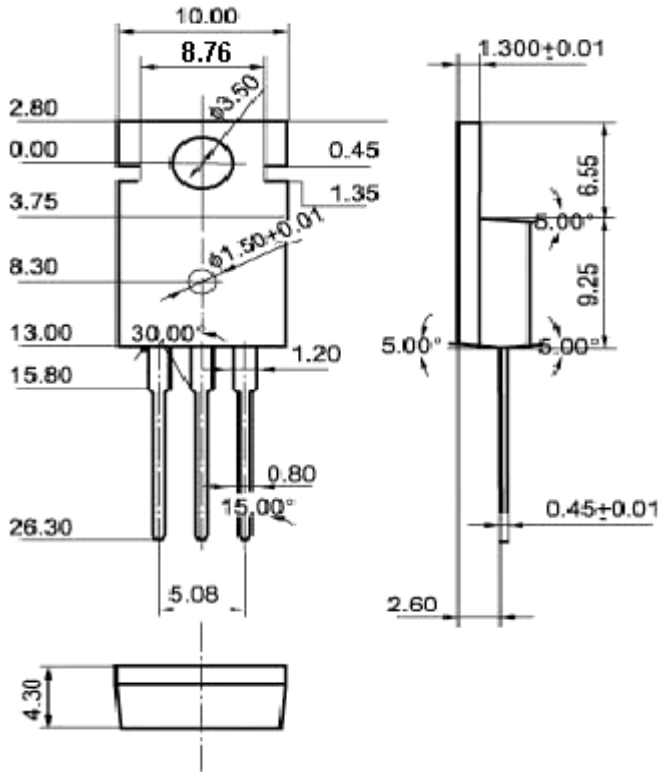

Fig.2 Outline dimensions (unindicated tolerance:±0.10mm)